

## DESCRIPTION

The CNY17F series consists of a Gallium Arsenide IRED coupled with an NPN phototransistor

## FEATURES

- High isolation voltage 5300 VAC RMS-1 minute, 7500 VAC PEAK-1 minute
- High  $BV_{CEO}$  minimum 70 volts
- Maximum switching time in saturation specified
- Underwriters Laboratory (UL) recognized file #E90700

## APPLICATIONS

- Power supply regulators
- Digital logic inputs
- Microprocessor inputs
- Appliance sensor systems
- Industrial controls

**CNY17F-1**

(CTR = 40%-80%)

**CNY17F-2**

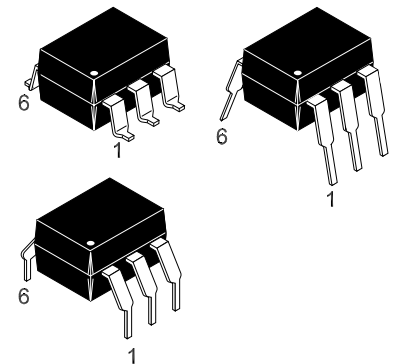
(CTR = 63%-125%)

**CNY17F-3**

(CTR = 100%-200%)

**CNY17F-4**

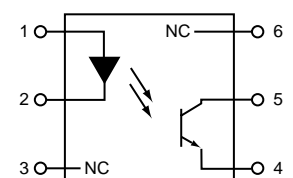
(CTR = 160%-320%)



## ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ Unless otherwise specified)

Rating	Symbol	Value	Unit
<b>INPUT LED</b>			
Forward Current - Continuous	$I_F$	90	mA
Forward Current - Peak (PW = 1 $\mu$ s, 300pps)	$I_F(\text{pk})$	3.0	A
Reverse Voltage	$V_R$	6	Volts
LED Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	135	mW
Derate above $25^\circ\text{C}$		1.8	mW/ $^\circ\text{C}$
<b>OUTPUT TRANSISTOR</b>			
Detector Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	200	mW
Derate above $25^\circ\text{C}$		2.67	mW/ $^\circ\text{C}$
<b>TOTAL DEVICE</b>			
Total Device Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	260	mW
Derate above $25^\circ\text{C}$		3.5	mW/ $^\circ\text{C}$
Ambient Operating Temperature Range	$T_A$	-55 to +100	$^\circ\text{C}$
Storage Temperature Range	$T_{\text{stg}}$	-55 to +150	$^\circ\text{C}$
Lead Soldering Temperature (1/16" from case, 10 sec. duration)	$T_L$	260	$^\circ\text{C}$

## SCHEMATIC



PIN 1. ANODE  
2. CATHODE  
3. NO CONNECTION  
4. EMITTER  
5. COLLECTOR  
6. NO CONNECTION

## NOTE

1. Input-Output Isolation Voltage, VISO, is an internal device dielectric breakdown rating.

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C Unless otherwise specified.)

### INDIVIDUAL COMPONENT CHARACTERISTICS

Parameter	Test Conditions	Symbol	Min	Typ**	Max	Unit
<b>EMITTER</b>						
Input Forward Voltage	(I <sub>F</sub> = 60 mA)	V <sub>F</sub>		1.35	1.65	V
Forward Voltage Temp. Coefficient		$\frac{\Delta V_F}{\Delta T_A}$		-1.8		mV/°C
Reverse Voltage	(I <sub>R</sub> = 10 μA)	V <sub>R</sub>	6.0	15		V
Junction Capacitance	(V <sub>F</sub> = 0 V, f = 1 MHz)	C <sub>J</sub>		50		pF
	(V <sub>F</sub> = 1 V, f = 1 MHz)			65		
Reverse Leakage Current	(V <sub>R</sub> = 3.0 V)	I <sub>R</sub>		.35	10	μA
<b>DETECTOR</b>						
Collector-Emitter Breakdown Voltage	(I <sub>C</sub> = 1.0 mA, I <sub>F</sub> = 0)	BV <sub>CEO</sub>	70	100		V
Emitter-Collector Breakdown Voltage	(I <sub>E</sub> = 100 μA, I <sub>F</sub> = 0)	BV <sub>ECO</sub>	7	10		V
Collector-Emitter Dark Current	(V <sub>CE</sub> = 10 V, I <sub>F</sub> = 0)	I <sub>CEO</sub>		5	50	nA
Capacitance	(V <sub>CE</sub> = 0 V, f = 1 MHz)	C <sub>CE</sub>		8		pF

### TRANSFER CHARACTERISTICS

AC Characteristic	Test Conditions	Symbol	Min	Typ**	Max	Units
<b>SWITCHING TIMES</b>						
Non-Saturated Turn-on Time	(R <sub>L</sub> = 100 Ω, I <sub>C</sub> = 2 mA, V <sub>CC</sub> = 10 V)	t <sub>on</sub>		6.0	10	μs
Turn-off Time		t <sub>off</sub>		5.5	10	μs
<b>SATURATED SWITCHING TIMES</b>						
Turn-on Time CNY17F-1	(I <sub>F</sub> = 20 mA, V <sub>CE</sub> = 0.4 V)	t <sub>on</sub>		3.0	5.5	μs
			CNY17F-2 CNY17F-3 CNY17F-4	(I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 0.4 V)		
Rise Time CNY17F-1	(I <sub>F</sub> = 20 mA, V <sub>CE</sub> = 0.4 V)	t <sub>r</sub>		2.0	4.0	μs
			CNY17F-2 CNY17F-3 CNY17F-4	(I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 0.4 V)		
Turn-off Time CNY17F-1	(I <sub>F</sub> = 20 mA, V <sub>CE</sub> = 0.4 V)	t <sub>off</sub>		18	34	μs
			CNY17F-2 CNY17F-3 CNY17F-4	(I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 0.4 V)		
Fall Time CNY17F-1	(I <sub>F</sub> = 20 mA, V <sub>CE</sub> = 0.4 V)	t <sub>f</sub>		11	20	μs
			CNY17F-2 CNY17F-3 CNY17F-4	(I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 0.4 V)		

\*\* All typicals at T<sub>A</sub> = 25°C

## TRANSFER CHARACTERISTICS

DC Characteristic	Test Conditions	Symbol	Min	Typ**	Max	Units
Current Transfer Ratio, Collector-Emitter	$(I_F = 10 \text{ mA}, V_{CE} = 5 \text{ V})$	CTR	40		80	%
CNY17F-1			63		125	
CNY17F-2			100		200	
CNY17F-3			160		320	
Saturation Voltage	$(I_F = 10 \text{ mA}, I_C = 2.5 \text{ mA})$	$V_{CE(sat)}$		0.15	0.40	V

## ISOLATION CHARACTERISTICS

Characteristic	Test Conditions	Symbol	Min	Typ**	Max	Units
Input-Output Isolation Voltage	$(I_{I-O} \leq 1 \mu\text{A}, 1 \text{ min.})$	$V_{ISO}$	5300			$V_{ac(rms)}$
			7500			$V_{ac(pk)}$
Isolation Resistance	$(V_{I-O} = 500 \text{ VDC})$	$R_{ISO}$	$10^{11}$			$\Omega$
Isolation Capacitance	$(f = 1 \text{ MHz})$	$C_{ISO}$		0.5		pf

\*\* All typicals at  $T_A = 25^\circ\text{C}$

### TYPICAL CHARACTERISTICS

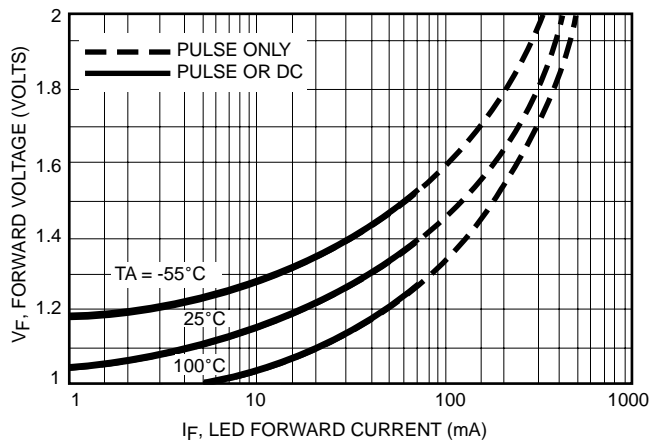


Figure 1. LED Forward Voltage versus Forward Current

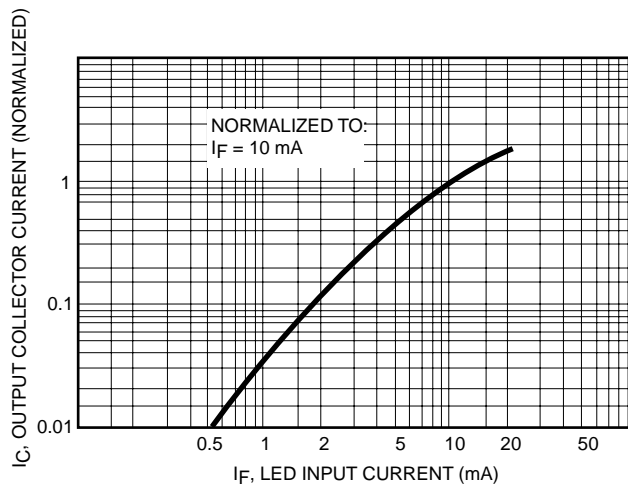


Figure 2. Output Current versus Input Current

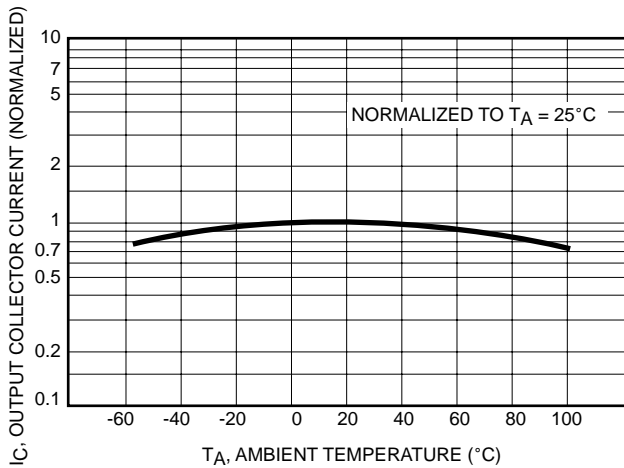


Figure 3. Output Current versus Ambient Temperature

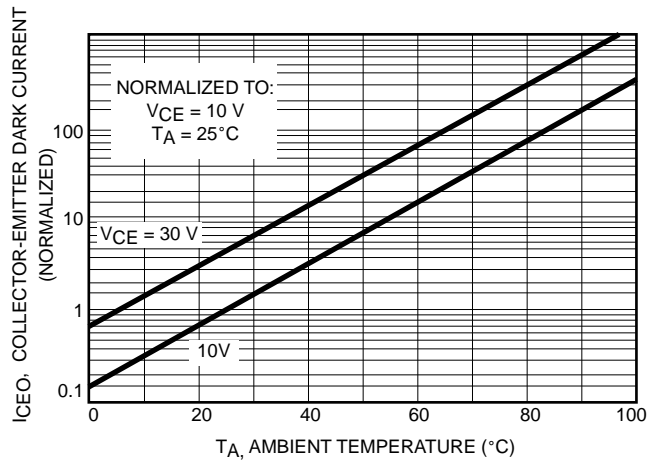


Figure 4. Dark Current versus Ambient Temperature

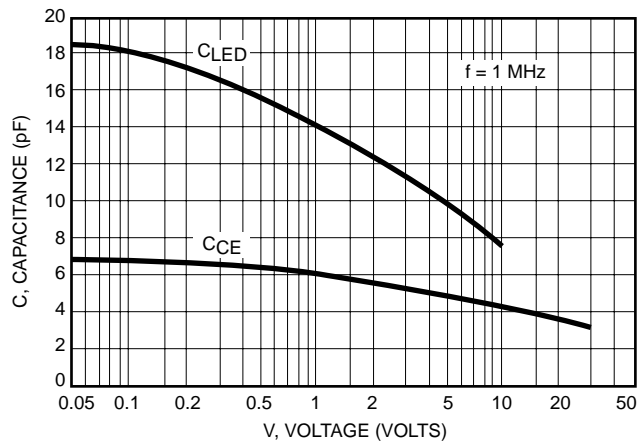


Figure 5. Capacitance versus Voltage

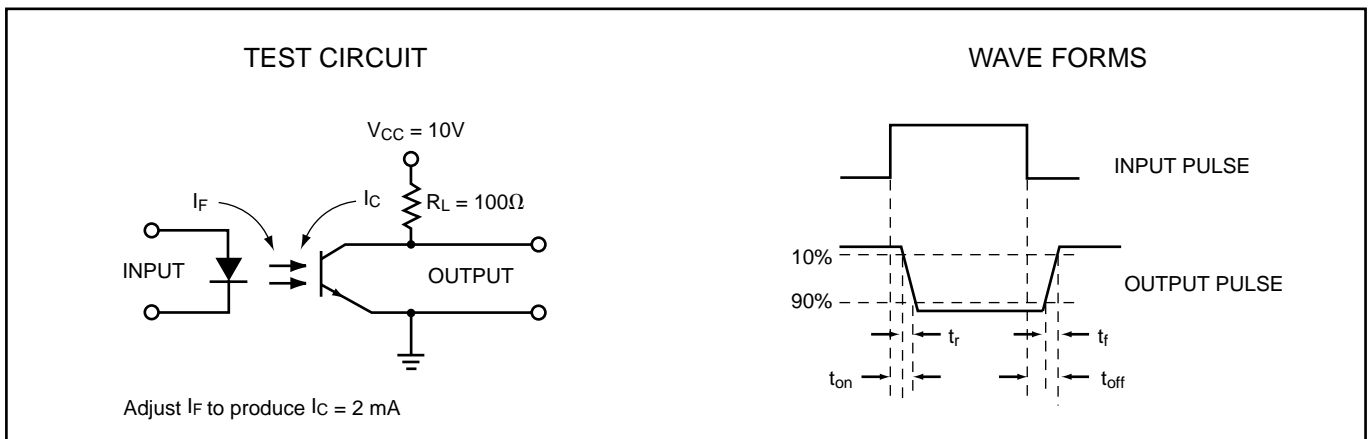
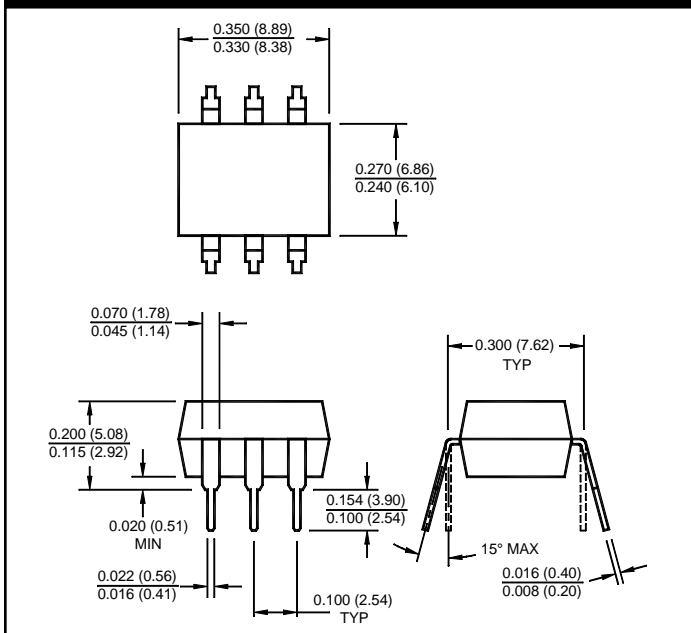
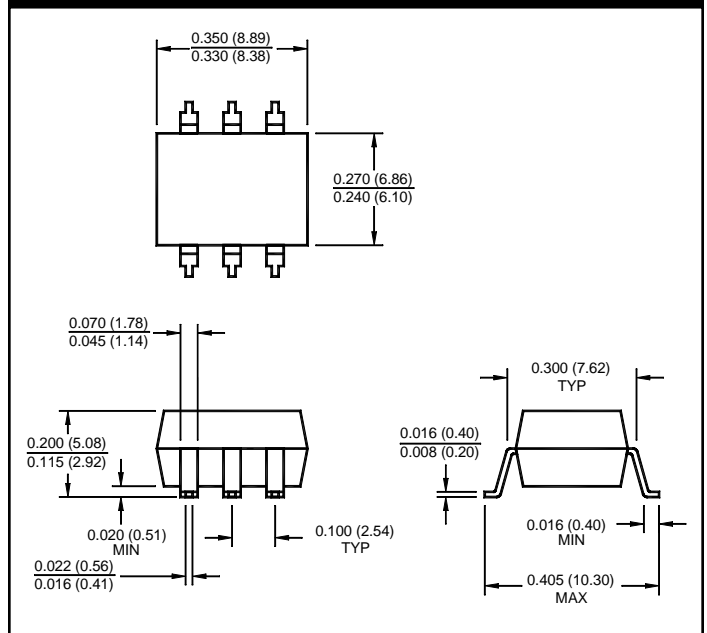


Figure 6. Switching Time Test Circuit and Waveforms

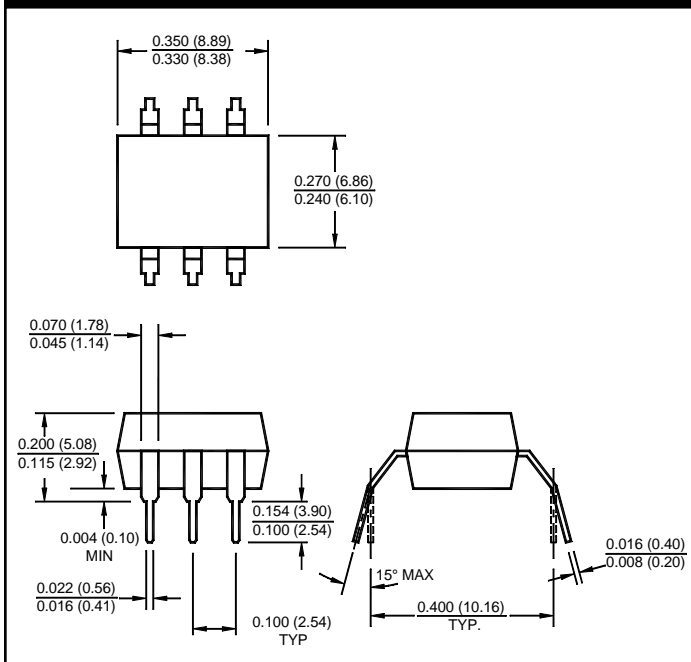
## Package Dimensions (Through Hole)



## Package Dimensions (Surface Mount)



## Package Dimensions (0.4" Lead Spacing)



### NOTE

All dimensions are in inches (millimeters)

**Call QT Optoelectronics for more information or the phone number of your nearest distributor.**

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